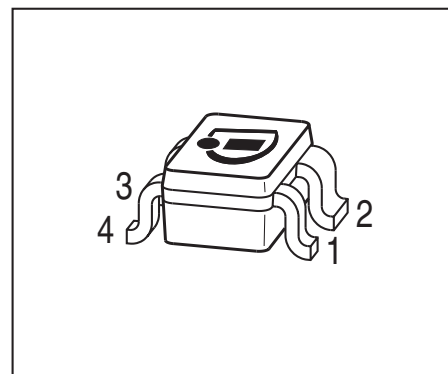


NPN Silicon RF Transistor

- For high gain low noise amplifiers
- For oscillators up to 10 GHz
- Noise figure $F = 1.1$ dB at 1.8 GHz
outstanding $G_{ms} = 21$ dB at 1.8 GHz
- Transition frequency $f_T = 25$ GHz
- Gold metallization for high reliability
- SIEGET[®] 25 GHz f_T - Line
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP420	AMs	1=B	2=E	3=C	4=E	-	-	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage $T_A > 0$ °C $T_A \leq 0$ °C	V_{CEO}	4.5 4.1	V
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	35	mA
Base current	I_B	3	
Total power dissipation ²⁾ $T_S \leq 107$ °C	P_{tot}	160	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

¹⁾Pb-containing package may be available upon special request

²⁾ T_S is measured on the collector lead at the soldering point to the pcb

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	≤ 260	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4.5	5	-	V
Collector-emitter cutoff current $V_{CE} = 15\text{ V}, V_{BE} = 0$	I_{CES}	-	-	10	μA
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 0.5\text{ V}, I_C = 0$	I_{EBO}	-	-	3	μA
DC current gain $I_C = 20\text{ mA}, V_{CE} = 4\text{ V}$, pulse measured	h_{FE}	60	95	130	-

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 30\text{ mA}$, $V_{CE} = 3\text{ V}$, $f = 2\text{ GHz}$	f_T	18	25	-	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.15	0.3	pF
Collector emitter capacitance $V_{CE} = 2\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.37	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	0.55	-	
Noise figure $I_C = 5\text{ mA}$, $V_{CE} = 2\text{ V}$, $f = 1.8\text{ GHz}$, $Z_S = Z_{Sopt}$	F	-	1.1	-	
Power gain, maximum stable ¹⁾ $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 1.8\text{ GHz}$	G_{ms}	-	21	-	dB
Insertion power gain $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\ \Omega$	$ S_{21} ^2$	14	17	-	
Third order intercept point at output ²⁾ $V_{CE} = 2\text{ V}$, $I_C = 20\text{ mA}$, $f = 1.8\text{ GHz}$, $Z_S = Z_L = 50\ \Omega$	IP_3	-	22	-	dBm
1dB Compression point at output $I_C = 20\text{ mA}$, $V_{CE} = 2\text{ V}$, $Z_S = Z_L = 50\ \Omega$, $f = 1.8\text{ GHz}$	P_{-1dB}	-	12	-	

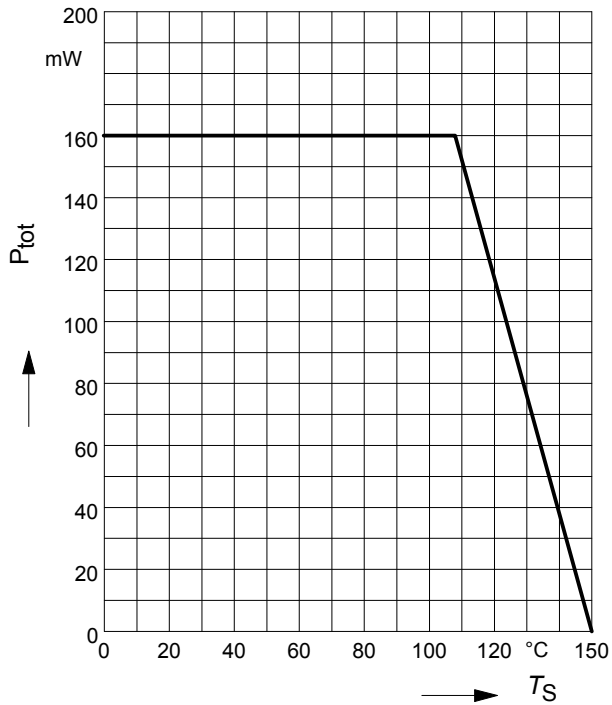
¹⁾ $G_{ms} = |S_{21}| / |S_{12}|$
²⁾ IP_3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is $50\ \Omega$ from 0.1 MHz to 6 GHz

Simulation Data

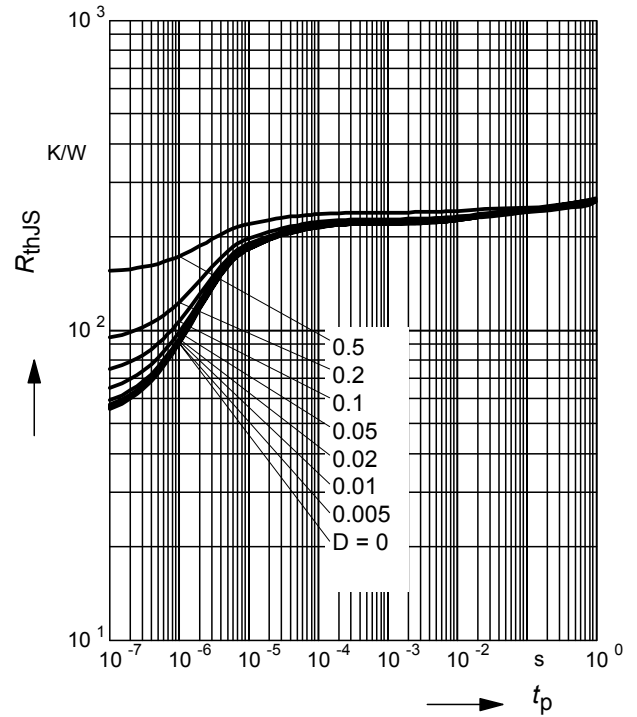
For SPICE-model as well as for S-parameters including noise parameters refer to our internet website: www.infineon.com/rf.models. Please consult our website and download the latest version before actually starting your design.

The simulation data have been generated and verified up to 10 GHz using typical devices. The BFP420 nonlinear SPICE-model reflects the typical DC- and RF-device performance with high accuracy.

Total power dissipation $P_{\text{tot}} = f(T_S)$

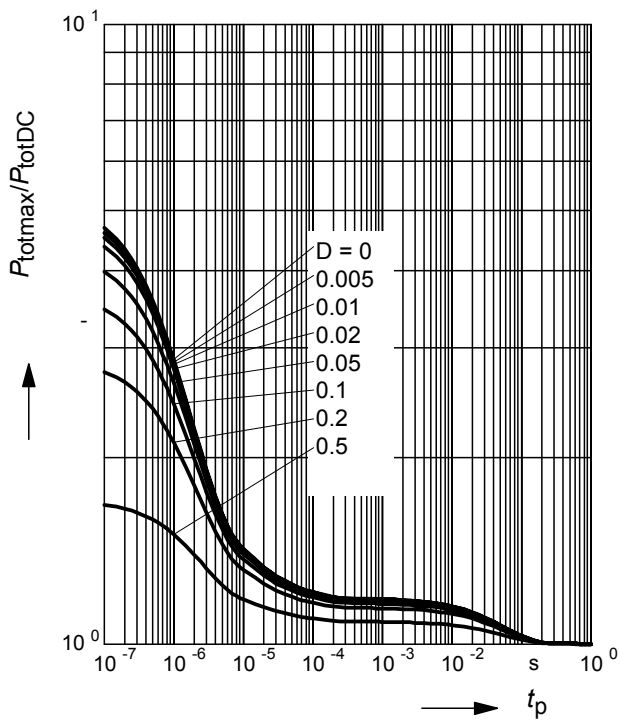


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



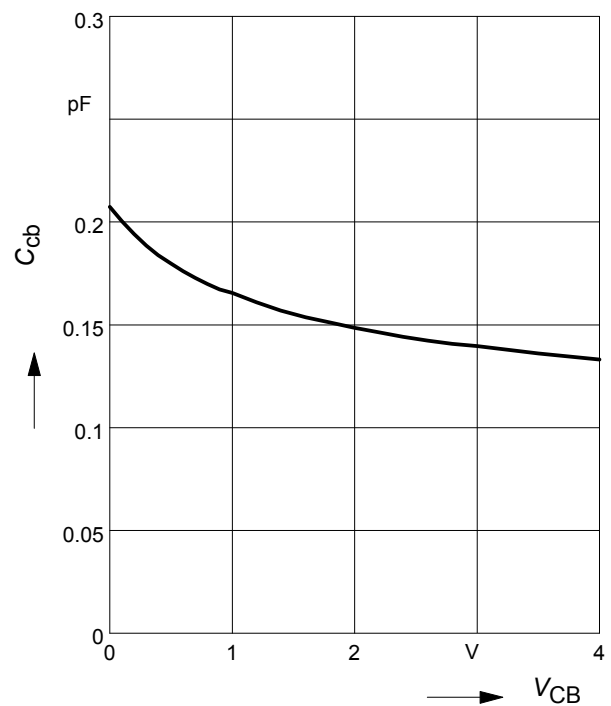
Permissible Pulse Load

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



Collector-base capacitance $C_{\text{cb}} = f(V_{\text{CB}})$

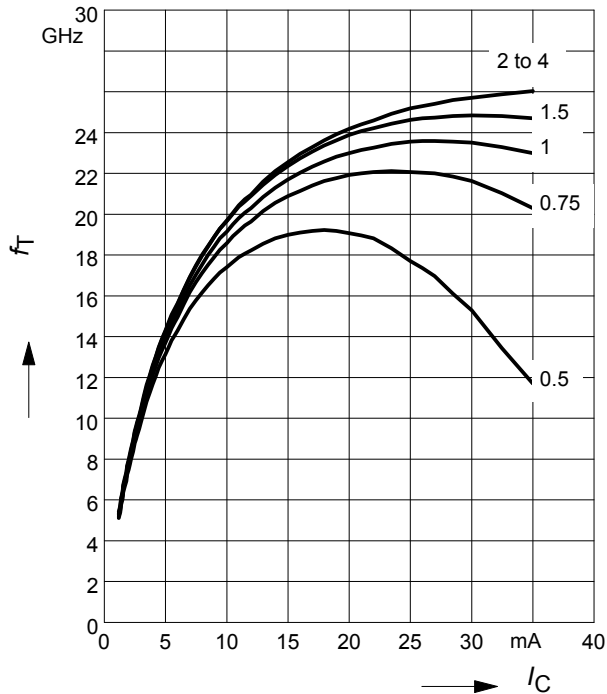
$f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

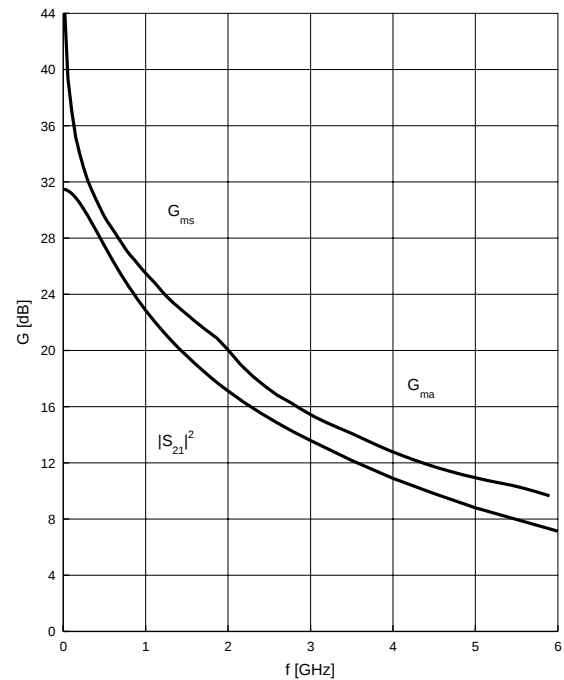
$f = 2 \text{ GHz}$

$V_{CE} = \text{parameter in V}$



Power gain $G_{ma}, G_{ms}, |S_{21}|^2 = f(f)$

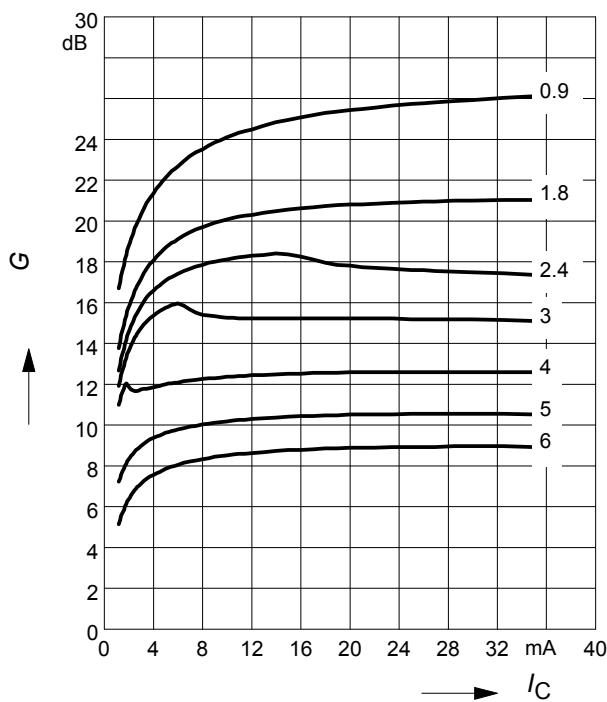
$V_{CE} = 2 \text{ V}, I_C = 20 \text{ mA}$



Power gain $G_{ma}, G_{ms} = f(I_C)$

$V_{CE} = 2 \text{ V}$

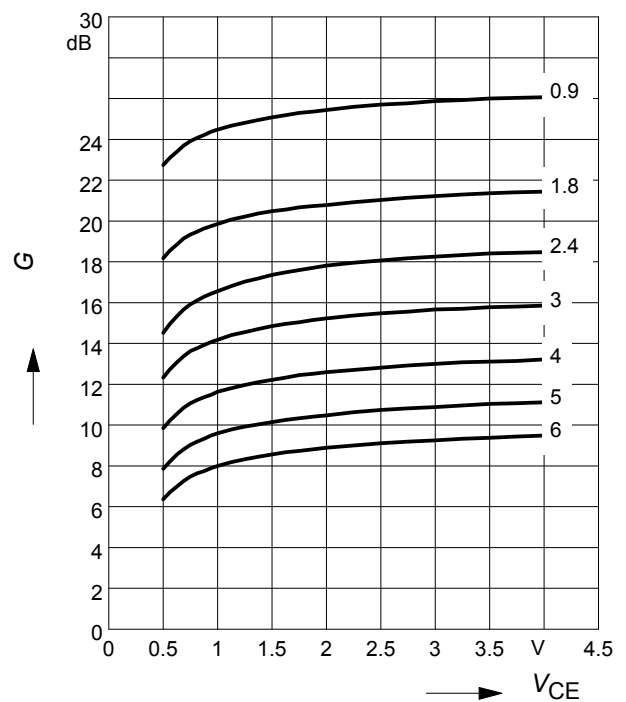
$f = \text{parameter in GHz}$



Power gain $G_{ma}, G_{ms} = f(V_{CE})$

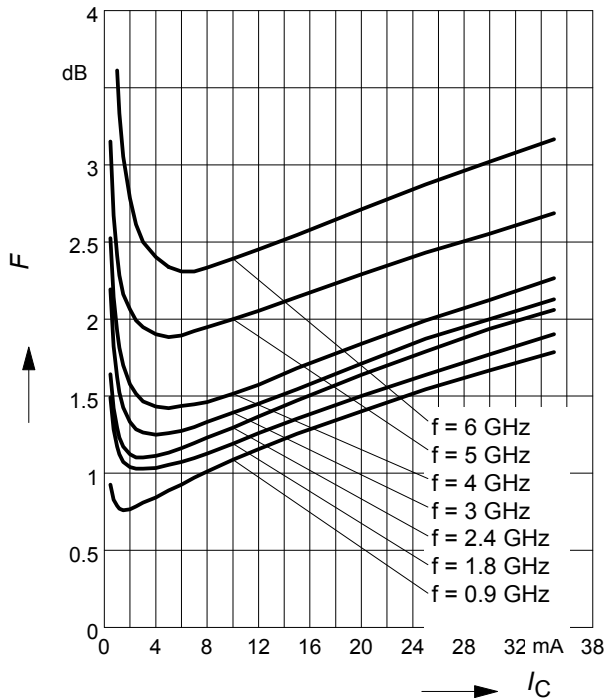
$I_C = 20 \text{ mA}$

$f = \text{parameter in GHz}$



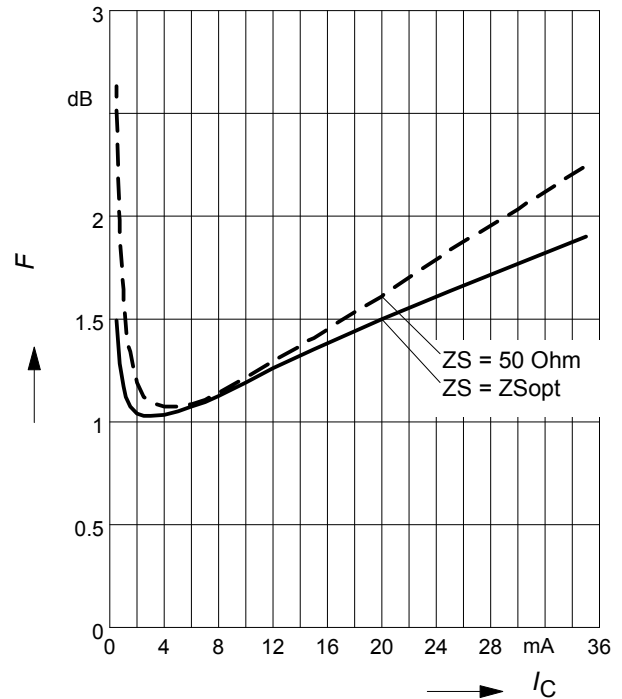
Noise figure $F = f(I_C)$

$V_{CE} = 2 \text{ V}$, $Z_S = Z_{Sopt}$



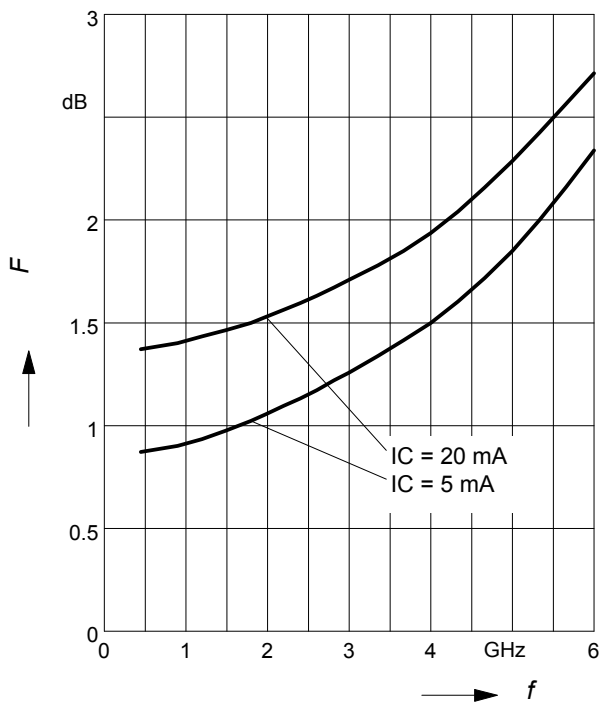
Noise figure $F = f(I_C)$

$V_{CE} = 2 \text{ V}$, $f = 1.8 \text{ GHz}$



Noise figure $F = f(f)$

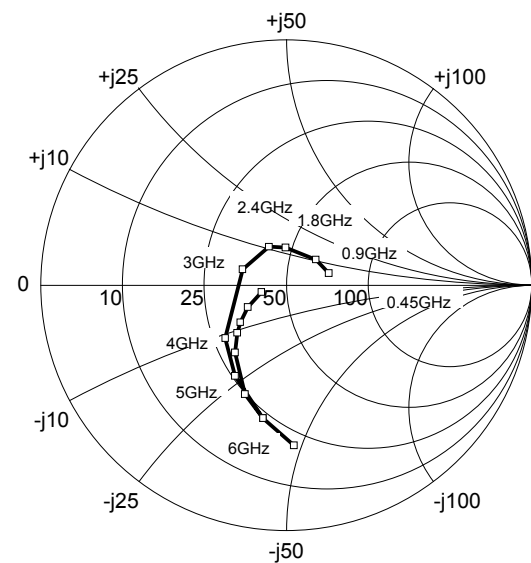
$V_{CE} = 2 \text{ V}$, $Z_S = Z_{Sopt}$



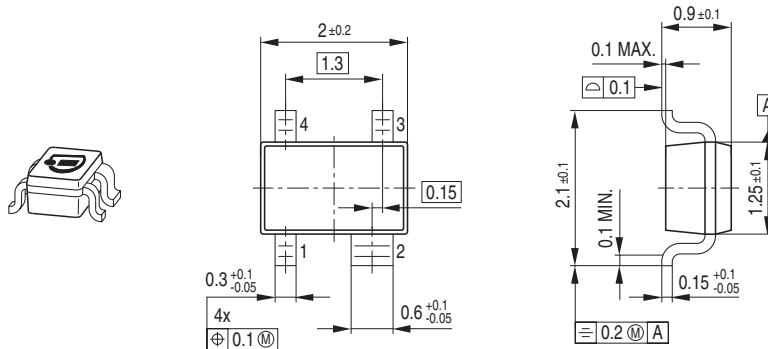
Source impedance for min.

noise figure vs. frequency

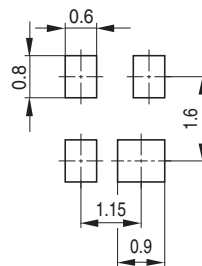
$V_{CE} = 2 \text{ V}$, $I_C = 5 \text{ mA} / 20 \text{ mA}$



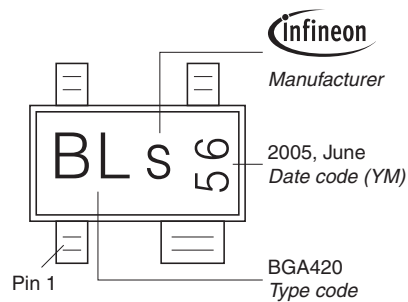
Package Outline



Foot Print

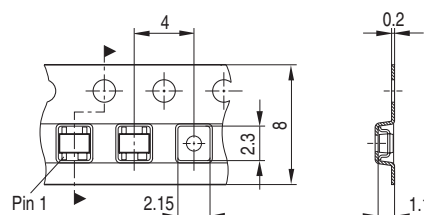


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



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